## Nch 600V 9A Power MOSFET

$V_{DSS}$	600V
R <sub>DS(on)</sub> (Max.)	0.535Ω
I <sub>D</sub>	±9A
P <sub>D</sub>	48W

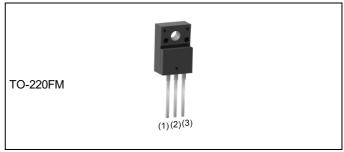
# ●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V<sub>GSS</sub>) guaranteed to be ±20V.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

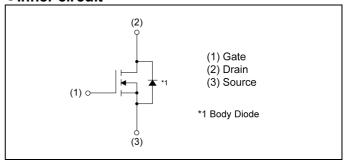
## Application

Switching

### Outline



## ●Inner circuit



Packaging specifications

	, , ,	
	Packing	Bulk
	Reel size (mm)	-
T	Tape width (mm)	-
Type	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	R6009ENX

## ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		V <sub>DSS</sub>	600	V
Continuous dusin summert	T <sub>C</sub> = 25°C	I <sub>D</sub> *1	±9	А
Continuous drain current	T <sub>C</sub> = 100°C	I <sub>D</sub> *1	±4.9	Α
Pulsed drain current	·	I <sub>DP</sub> *2	±18	Α
Cata Saurea valtaga	static	V	±20	V
Gate - Source voltage	AC(f>1Hz)	$V_{GSS}$	±30	V
Avalanche current, repetitive	·	I <sub>AR</sub>	1.4	Α
Avalanche energy, single pulse		E <sub>AS</sub> *3	153	mJ
Avalanche energy, repetitive		E <sub>AR</sub> *3	0.23	mJ
Power dissipation (T <sub>C</sub> = 25°C)		P <sub>D</sub> *4	48	W
Junction temperature	T <sub>j</sub>	150	°C	
Operating junction and storage tem	perature range	T <sub>stg</sub>	-55 <b>~</b> +150	°C

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values	Unit
Reverse diode dv/dt	dv/dt	-	15	V/ns
Drain - Source voltage slope	dv/dt	V <sub>DS</sub> = 480V, T <sub>j</sub> = 25°C	50	V/ns

## ●Thermal resistance

Downwortow	Cymab al	Values			Lleit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub>	-	-	2.6	°C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	70	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	°C

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit	
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	UIIIL	
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V$ , $I_D = 1mA$	600	-	1	V	
		V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V					
Zero gate voltage drain current	I <sub>DSS</sub>	T <sub>j</sub> = 25°C	-	0.1	100	μA	
drain ourione		T <sub>j</sub> = 125°C	1	-	1000		
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA	
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	2	-	4	V	
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.8A					
Static drain - source on - state resistance	R <sub>DS(on)</sub> *5	T <sub>j</sub> = 25°C	-	0.500	0.535	Ω	
on state recipiantes		T <sub>j</sub> = 125°C	-	1.00	-		
Gate resistance	R <sub>G</sub>	f =1MHz, open drain	-	9.6	-	Ω	

## ● Electrical characteristics (T<sub>a</sub> = 25°C)

Dougnoston	Corrects and	Conditions		l leit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward Transfer Admittance	Y <sub>fs</sub>  *5	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A	2.3	4.5	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	430	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 25V	-	470	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	55	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V	-	23	-	. F
Effective output capacitance, time related	C <sub>o(tr)</sub>	V <sub>DS</sub> = 0V to 480V	-	100	-	pF
Turn - on delay time	t <sub>d(on)</sub> *5	V <sub>DD</sub> ≈ 300V,V <sub>GS</sub> = 10V	-	25	-	
Rise time	t <sub>r</sub> *5	I <sub>D</sub> = 4.5A	-	35	-	
Turn - off delay time	t <sub>d(off)</sub> *5	R <sub>L</sub> ≃ 66.7Ω	-	75	-	ns
Fall time	t <sub>f</sub> *5	$R_G = 10\Omega$		30	-	

## ● Gate charge characteristics (T<sub>a</sub> = 25°C)

Darameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*5}$	V <sub>DD</sub> ≈ 300V,	-	23	-	
Gate - Source charge	Q <sub>gs</sub> *5	I <sub>D</sub> = 9.0A,	-	4	-	nC
Gate - Drain charge	Q <sub>gd</sub> *5	V <sub>GS</sub> = 10V	-	15	-	
Gate plateau voltage	V <sub>(plateau)</sub>	V <sub>DD</sub> = 300V, I <sub>D</sub> = 9A	-	6.4	-	V

<sup>\*1</sup> Limited only by maximum channel temperature allowed.

\*5 Pulsed

<sup>\*2</sup> Pw ≤ 10µs, Duty cycle ≤ 1%

<sup>\*3</sup> L  $\stackrel{.}{=}$  100mH, V<sub>DD</sub>=50V, R<sub>G</sub>=25 $\Omega$ , STARTING T<sub>j</sub>=25 $^{\circ}$ C

<sup>\*4</sup> T<sub>C</sub>=25°C

## ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions			Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Continuous forward current	I <sub>S</sub> *1	T <sub>c</sub> = 25°C	1	1	9	А	
Pulse forward current	l <sub>SP</sub> *2	1 <sub>c</sub> - 25 C	-	-	18	Α	
Forward voltage	V <sub>SD</sub> *5	V <sub>GS</sub> = 0V, I <sub>S</sub> = 9.0A	-	-	1.5	V	
Reverse recovery time	t <sub>rr</sub> *5		1	380	1	ns	
Reverse recovery charge	$Q_{rr}^{*5}$	I <sub>S</sub> = 9A, V <sub>GS</sub> =0V   di/dt = 100A/µs	-	3.8	-	μC	
Peak reverse recovery current	I <sub>mm</sub> *5	α,, ατ 100, τμο	-	20	-	Α	

● Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R <sub>th1</sub>	0.344		C <sub>th1</sub>	0.00137	
R <sub>th2</sub>	1.15	K/W	C <sub>th2</sub>	0.0145	Ws/K
R <sub>th3</sub>	2.2		C <sub>th3</sub>	0.451	

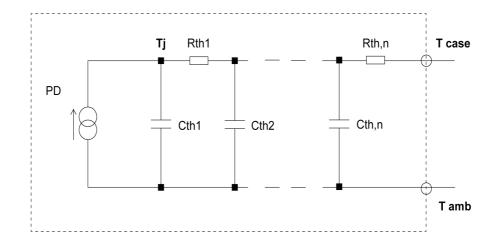


Fig.1 Power Dissipation Derating Curve

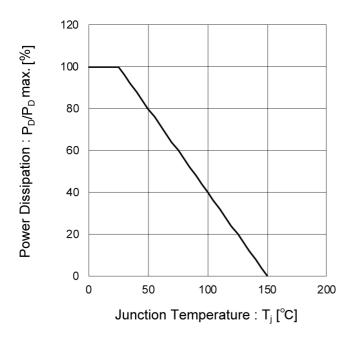


Fig.2 Maximum Safe Operating Area

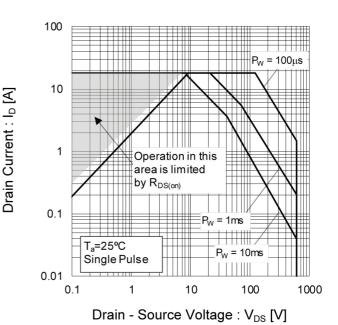


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

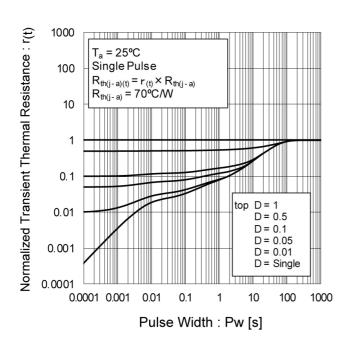
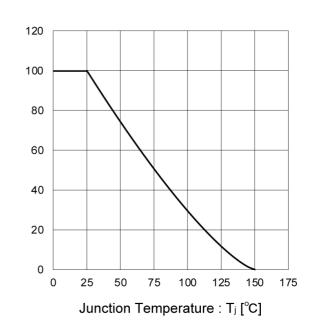


Fig.4 Avalanche Energy Derating
Curve vs. Junction Temperature



Avalanche Energy :  $\mathsf{E}_\mathsf{AS}$  /  $\mathsf{E}_\mathsf{AS}$  max [%]

Fig.5 Typical Output Characteristics(I)

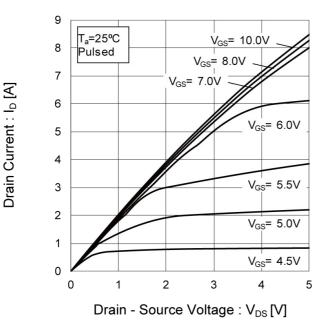
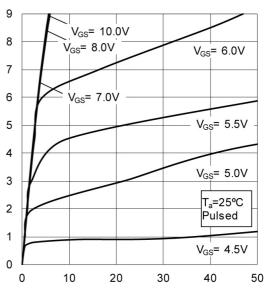


Fig.6 Typical Output Characteristics(II)



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.7 Tj = 150°C Typical Output Characteristics (I)

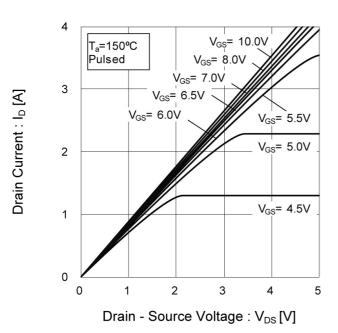
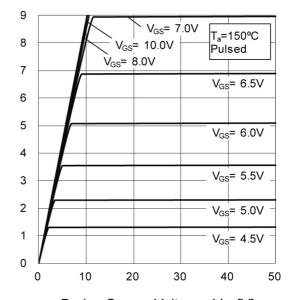


Fig.8 Tj = 150°C Typical Output Characteristics (II)



Drain Current : I<sub>D</sub> [A]

Drain Current : I<sub>D</sub> [A]

Fig.9 Breakdown Voltage vs.

Junction Temperature

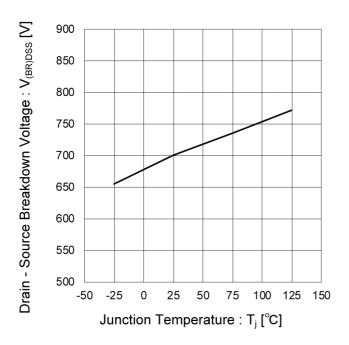


Fig.10 Typical Transfer Characteristics

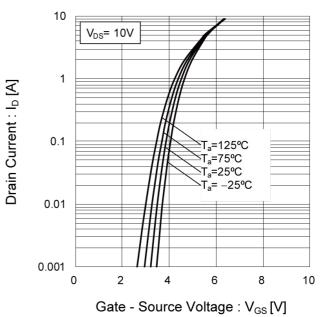


Fig.11 Gate Threshold Voltage vs.

Junction Temperature

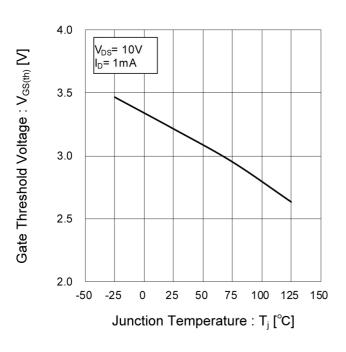


Fig.12 Forward Transfer Admittance vs.
Drain Current

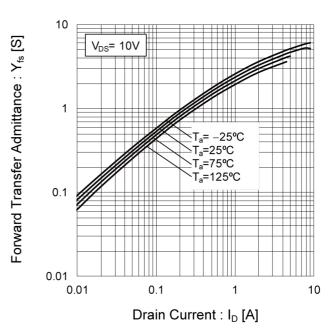


Fig.13 Static Drain - Source On - State
Resistance vs. Gate Source Voltage

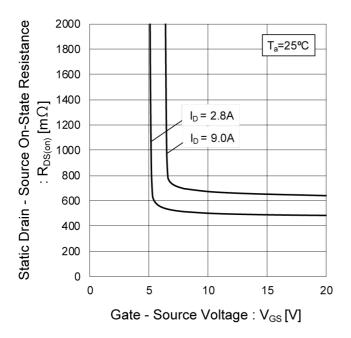


Fig.14 Static Drain - Source On - State
Resistance vs. Junction Temperature

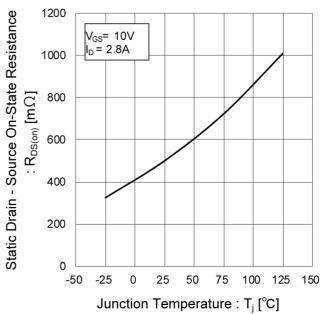


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(I)

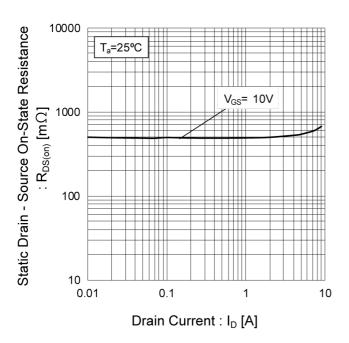
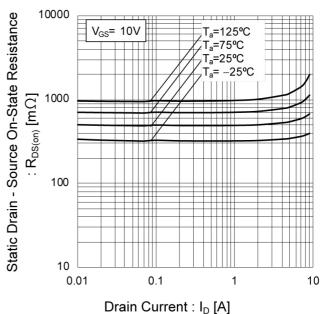


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(II)



8/12

Fig.17 Typical Capacitance vs. Drain - Source Voltage

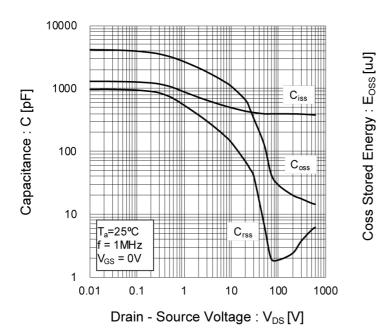


Fig.18 Coss Stored Energy

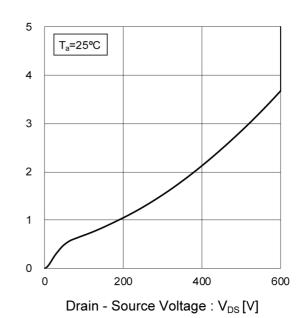


Fig.19 Switching Characteristics

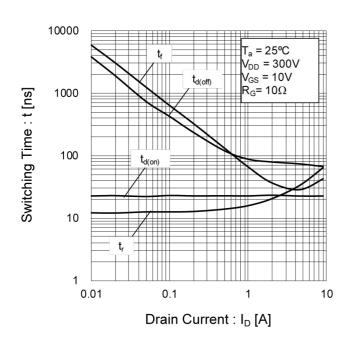
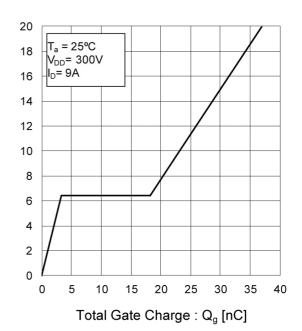


Fig.20 Dynamic Input Characteristics



Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.21 Inverse Diode Forward Current vs. Source - Drain Voltage

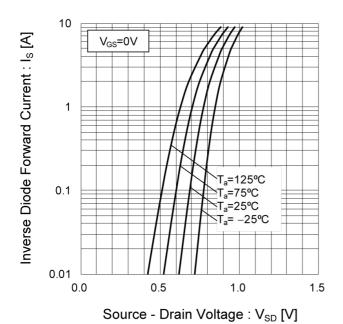
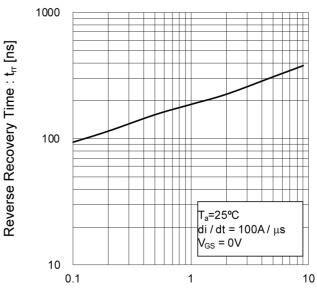


Fig.22 Reverse Recovery Time vs.
Inverse Diode Forward Current



### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

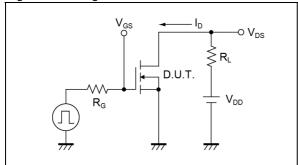


Fig.2-1 Gate Charge Measurement Circuit

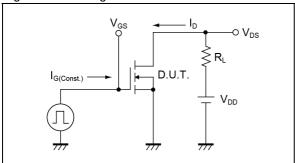


Fig.3-1 Avalanche Measurement Circuit

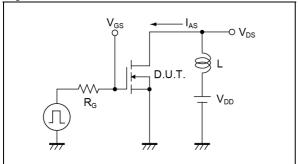


Fig.4-1 dv/dt Measurement Circuit

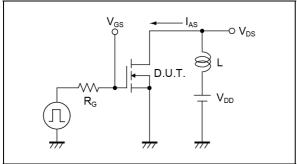


Fig.5-1 dv/dt Measurement Circuit

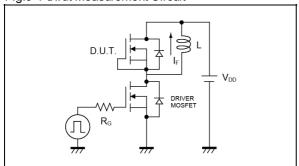


Fig.1-2 Switching Waveforms

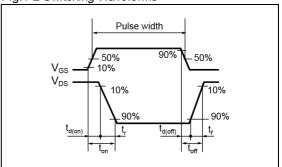


Fig.2-2 Gate Charge Waveform

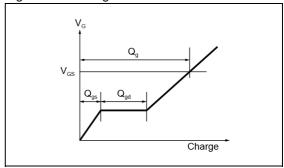


Fig.3-2 Avalanche Waveform

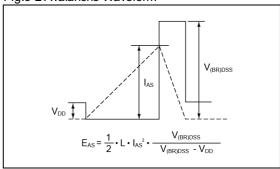


Fig.4-2 dv/dt Waveform

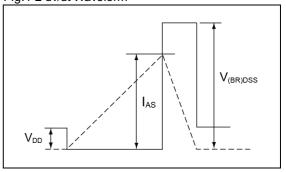
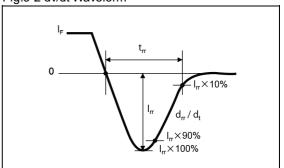
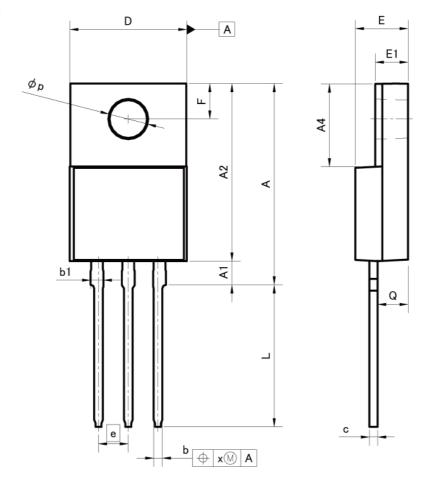


Fig.5-2 dv/dt Waveform



## Dimensions

TO-220FM



DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.90	0.028	0.035
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.390	0.406
E	4.40	4.80	0.173	0.189
е	2.9	54	0.1	00
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.110	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
Х	W <b>_</b>	0.38	_	0.015

Dimension in mm/inches



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JÁPAN	USA	EU	CHINA
CLASSⅢ	ОГУООШ	CLASS II b	CL ACCIII
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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  - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
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  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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